Nanoionics-based resistive switching memories

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Citation Report

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1215	/> <mml:mn>2</mml:mn> Cu <mml:math display="inline" xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mrow></mml:mrow> <mml:mn>3</mml:mn></mml:msub></mml:math> O <mml:math< td=""><td>3.2</td><td>24</td></mml:math<>	3.2	24
1216	xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"> <mml:msub> <mml:mrow></mml:mrow> <mml- Scaling Effect on Unipolar and Bipolar Resistive Switching of Metal Oxides. Scientific Reports, 2013, 3, 1657.</mml- </mml:msub>	3.3	87
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